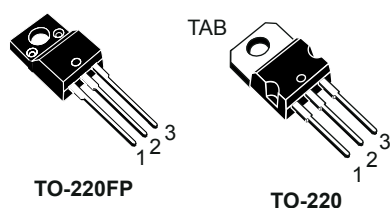


30 A, 600 V, fast IGBT



Features

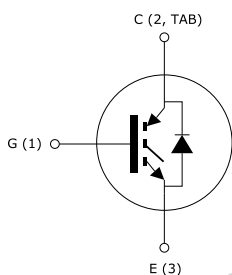
- Optimized performance for medium operating frequencies up to 5 kHz in hard switching
- Low on-voltage drop ($V_{CE(sat)}$)
- High current capability

Applications

- Motor drive

Description

These devices utilize the advanced PowerMESH process resulting in an excellent trade-off between switching performance and low on-state behavior.



Product status link

[STGF30NC60S](#)

[STGP30NC60S](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220	TO-220FP	
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$ V)	600		V
$I_C^{(1)}$	Continuous collector current at $T_C = 25$ °C	55	22	A
	Continuous collector current at $T_C = 100$ °C	35	11	
$I_{CL}^{(2)}$	Turn-off latching current	150		A
$I_{CP}^{(3)}$	Pulsed collector current	150		A
V_{GE}	Gate-emitter voltage	± 20		V
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1$ s, $T_C = 25$ °C)		2.5	kV
P_{TOT}	Total power dissipation at $T_C = 25$ °C	175	40	W
T_J	Operating junction temperature range	- 55 to 150		°C

1. Calculated according to the iterative formula: $I_C(T_C) = \frac{T_{J(max)} - T_C}{R_{thj} - C \times V_{CE(sat)(max)}(T_{J(max)}, I_C(T_C))}$
2. $V_{clamp} = 80\%(V_{CES})$, $T_J = 150$ °C, $R_G = 10$ Ω , $V_{GE} = 15$ V.
3. Pulse width limited by maximum junction temperature and turn-off within RBSOA.

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		TO-220	TO-220FP	
R_{thJC}	Thermal resistance junction-case	0.7	3.1	°C/W
R_{thJA}	Thermal resistance junction-ambient	62.5		°C/W

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$		1.5	1.9	V
		$V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$, $T_J = 150\text{ °C}$		1.4		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$			150	μA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 150\text{ °C}$			1	mA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 15\text{ V}$, $I_C = 20\text{ A}$		10		S

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	2200	-	pF
C_{oes}	Output capacitance		-	185	-	
C_{res}	Reverse transfer capacitance		-	48.5	-	
Q_g	Total gate charge	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$, $V_{GE} = 15\text{ V}$ (see Figure 18. Gate charge test circuit)	-	96	-	nC
Q_{ge}	Gate-emitter charge		-	14	-	
Q_{gc}	Gate-collector charge		-	44.5	-	

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$,	-	21.5	-	ns
t_r	Current rise time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$	-	8.5	-	ns
$(di/dt)_{on}$	Turn-on current slope	(see Figure 17. Test circuit for inductive load switching)	-	2280	-	A/ μ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$,	-	20.5	-	ns
t_r	Current rise time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	9.5	-	ns
$(di/dt)_{on}$	Turn-on current slope	(see Figure 17. Test circuit for inductive load switching)	-	2150	-	A/ μ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$,	-	85	-	ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$	-	180	-	ns
t_f	Current fall time	(see Figure 17. Test circuit for inductive load switching)	-	200	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$,	-	155	-	ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	260	-	ns
t_f	Current fall time	(see Figure 17. Test circuit for inductive load switching)	-	295	-	ns

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	$V_{CE} = 480\text{ V}$, $I_C = 20\text{ A}$,	-	300	-	μ J
E_{off}	Turn-off switching energy	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$	-	1275	-	μ J
E_{ts}	Total switching energy	(see Figure 17. Test circuit for inductive load switching)	-	1575	-	μ J
E_{on}	Turn-on switching energy	$V_{CE} = 480\text{ V}$, $I_C = 20\text{ A}$,	-	430	-	μ J
E_{off}	Turn-off switching energy	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	1965	-	μ J
E_{ts}	Total switching energy	(see Figure 17. Test circuit for inductive load switching)	-	2395	-	μ J

1. Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

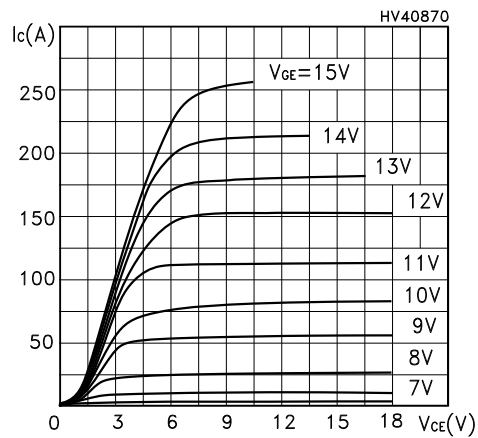
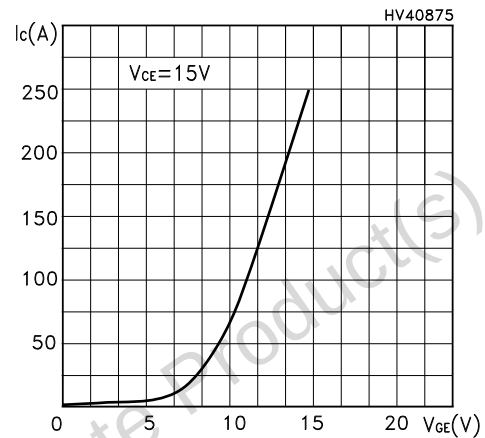
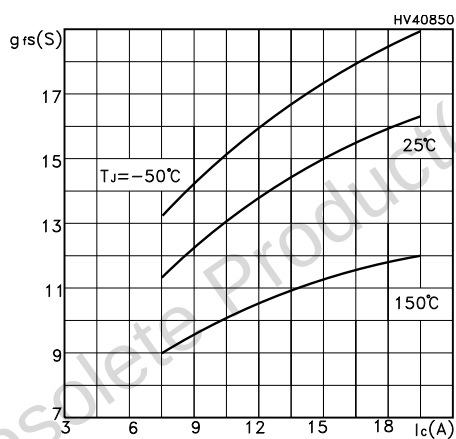
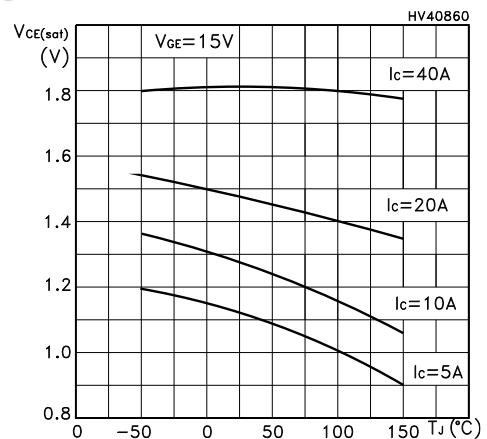
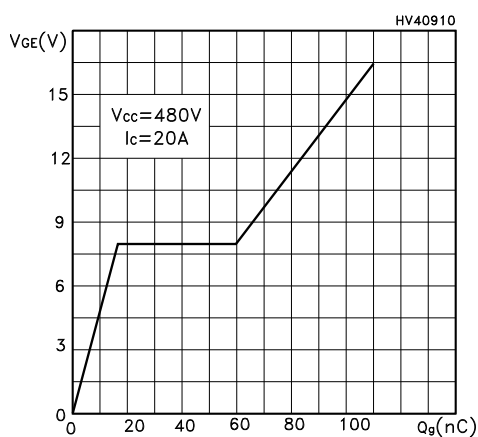
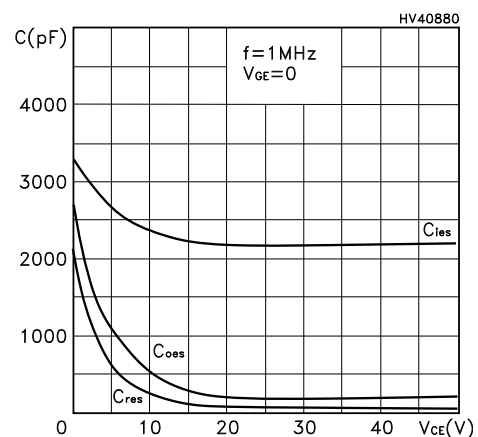
Figure 1. Output characteristics

Figure 2. Transfer characteristics

Figure 3. Transconductance

Figure 4. Collector-emitter on voltage vs temperature

Figure 5. Gate charge vs gate-source voltage

Figure 6. Capacitance variations


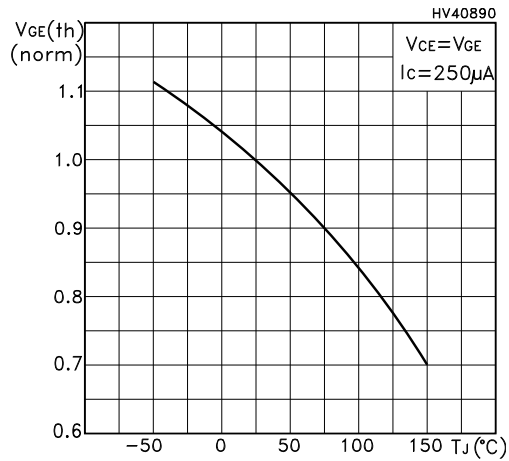
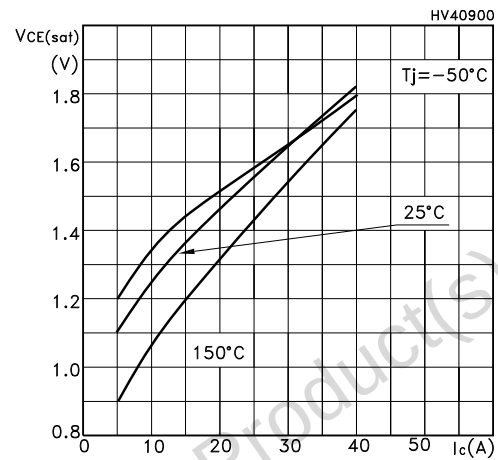
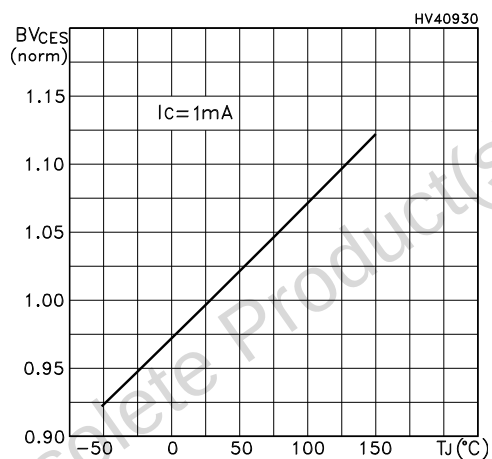
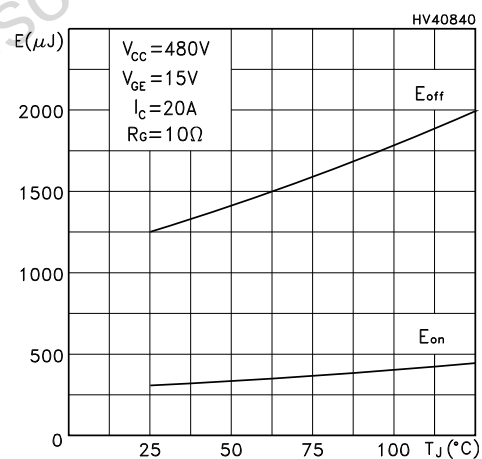
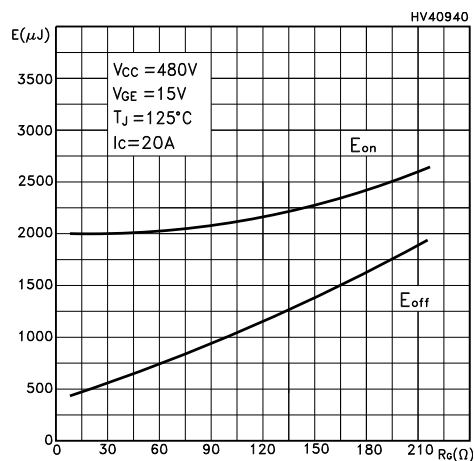
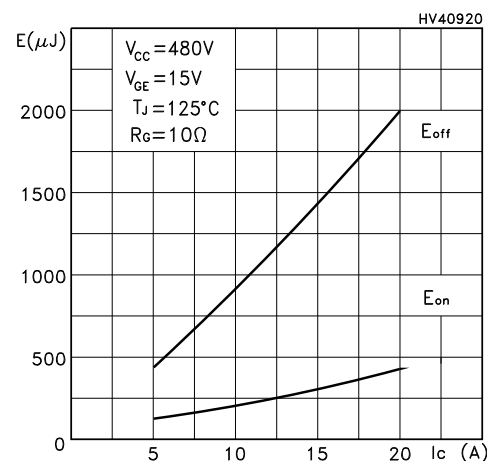
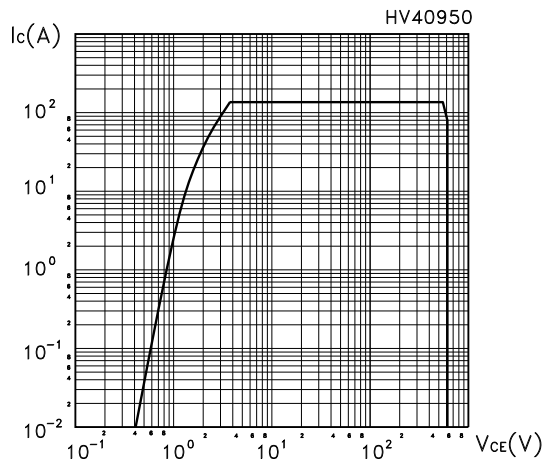
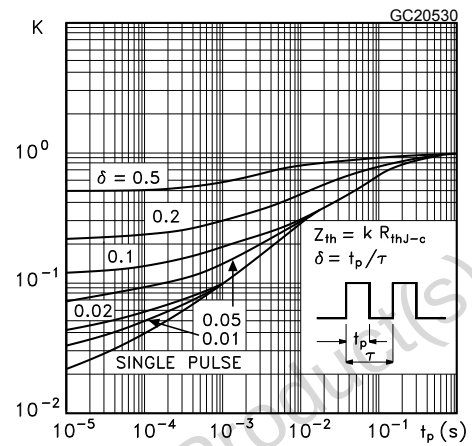
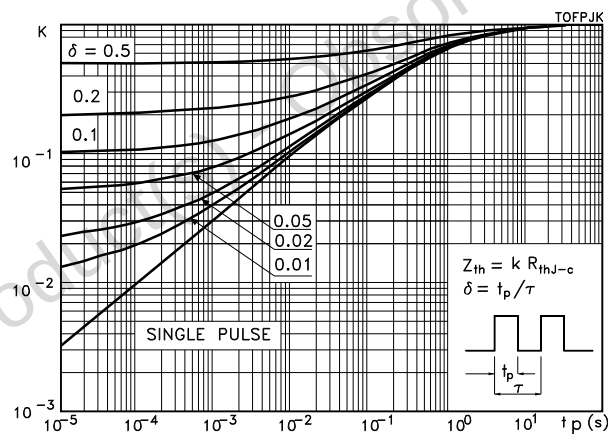
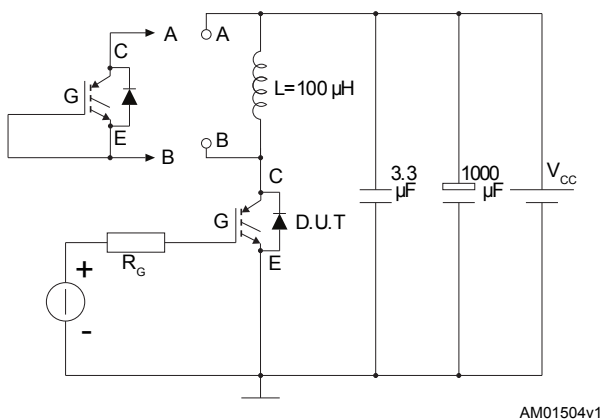
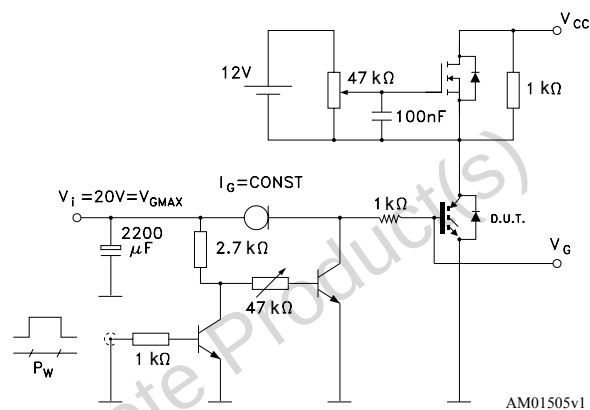
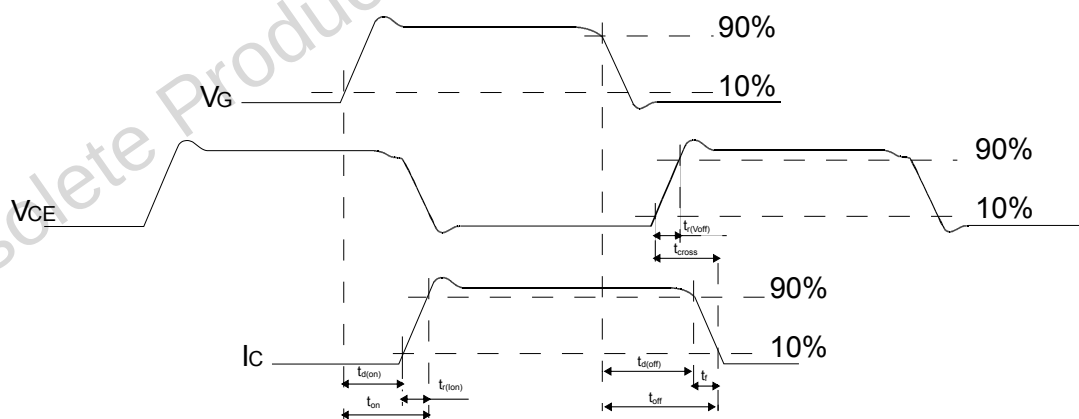
Figure 7. Normalized gate threshold voltage vs temperature

Figure 8. Collector-emitter on voltage vs collector current

Figure 9. Normalized breakdown voltage vs temperature

Figure 10. Switching losses vs temperature

Figure 11. Switching losses vs gate resistance

Figure 12. Switching losses vs collector current


Figure 13. Turn-off SOA

Figure 14. Thermal Impedance for TO-220

Figure 15. Thermal Impedance for TO-220FP


3 Test circuits

Figure 16. Test circuit for inductive load switching

Figure 17. Gate charge test circuit

Figure 18. Switching waveform


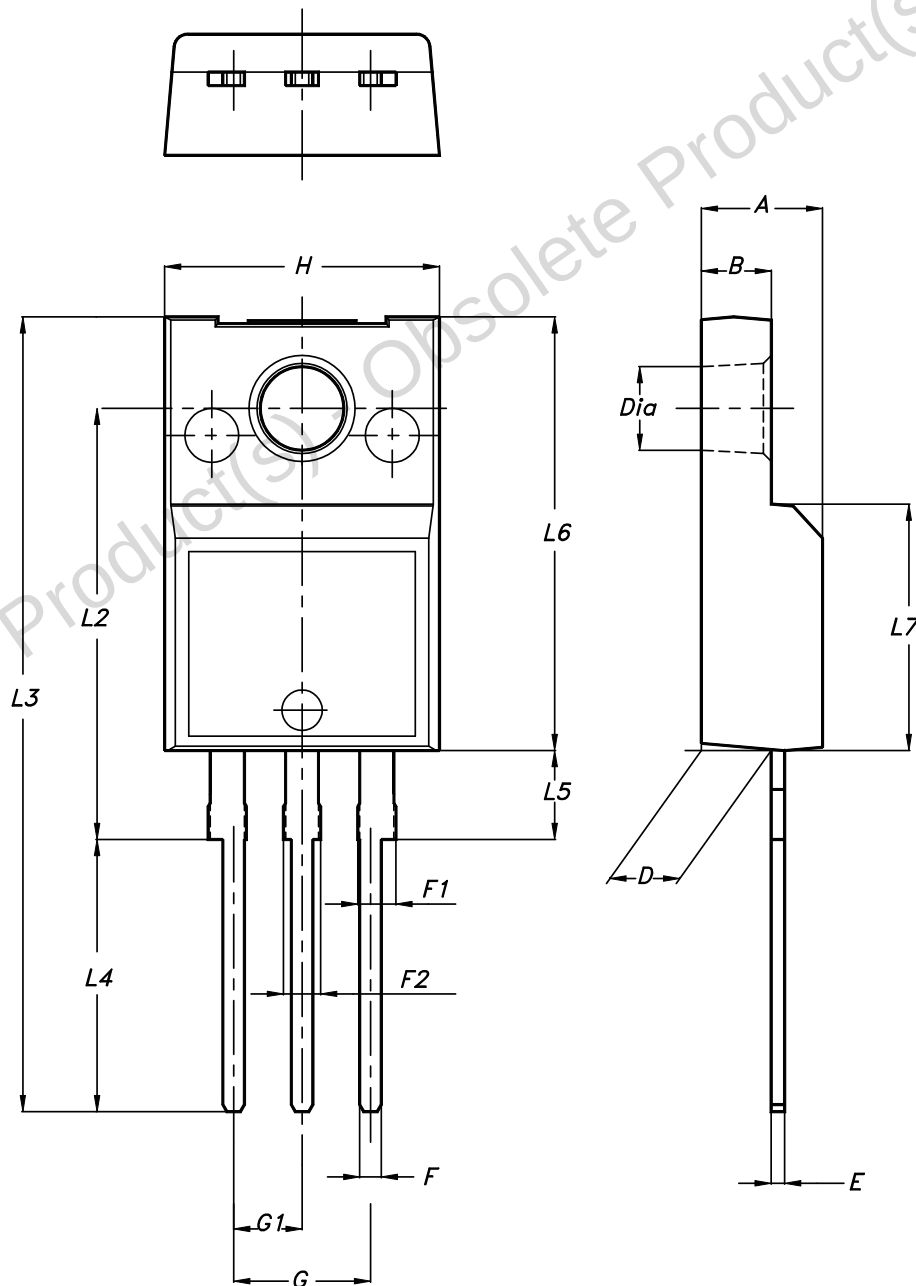
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP package information

Figure 19. TO-220FP package outline



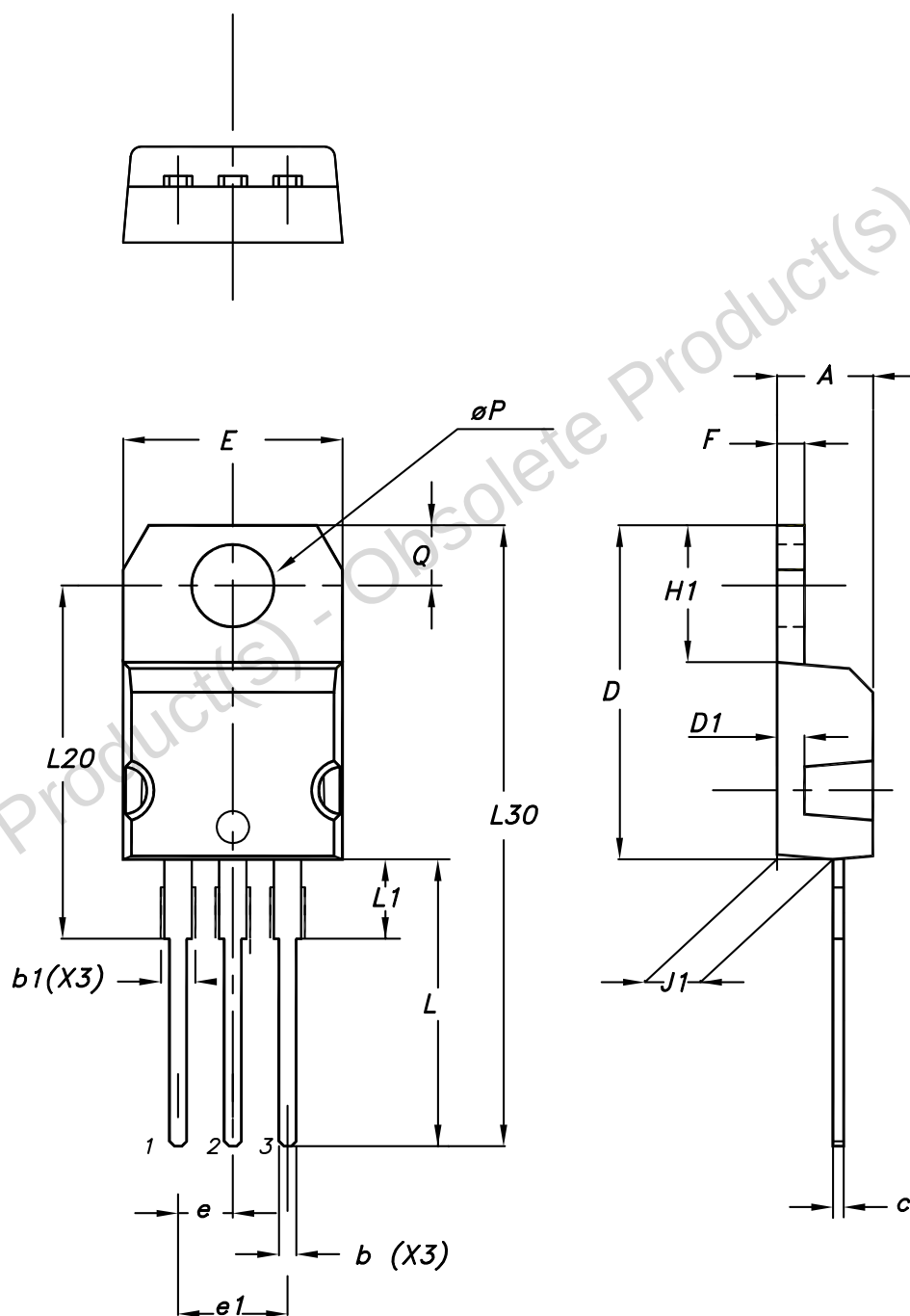
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Table 7. TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.2 TO-220 type A package information

Figure 20. TO-220 type A package outline



0015988_typeA_Rev_23

Table 8. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

5 Ordering information

Table 9. Order codes

Order code	Marking	Package	Packing
STGF30NC60S	GF30NC60S	TO-220FP	Tube
STGP30NC60S	GP30NC60S	TO-220	

Obsolete Product(s) - Obsolete Product(s)

Revision history

Table 10. Document revision history

Date	Revision	Changes
12-May-2020	1	First release. Part numbers previously included in datasheet DS5369.

Obsolete Product(s) - Obsolete Product(s)

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